exposing said first conductive layer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof to reduce an ability of the first conductive layer to associate with oxygen; and

forming the second conductive layer on the first conductive layer, the second conductive layer being formed after the first conductive layer has been exposed to the selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof.

92. (New) The method of claim 91, wherein providing a capacitor comprises providing an in-process capacitor; and the method further comprises providing a second conductive layer over the first conductive layer.

93. (New) The method of claim ~~92~~ 91 wherein the first conductive layer and the second conductive layer form a top plate of the capacitor.

94. (New) A method of treating a semiconductor device, comprising:

providing a capacitor having a first plate, a dielectric on the first plate, a first conductive layer on the dielectric with the first conductive layer having an ability to associate with oxygen, an oxide layer on the first conductive layer, and a second conductive layer on the oxide layer;

exposing the capacitor to a thermal process; and

prior to exposure to the thermal process and prior to forming the second conductive layer on the first conductive layer, exposing the first conductive layer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof to reduce an amount of oxygen associated with the first conductive material during formation of the second conductive layer and reduce a thickness of the oxide layer subsequently formed between the first and second conductive layers during exposure of the capacitor to the thermal process.

9 8

~~95.~~ (New) The method of claim ~~94~~ wherein the thickness of the oxide layer is less than approximately 10 angstroms.

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~~96.~~ (New) The method of claim ~~94~~ wherein the oxide layer comprises silicon dioxide.

11 8

~~97.~~ (New) The method of claim ~~94~~ wherein the dielectric comprises tantalum pentoxide.

12 8

~~98.~~ (New) The method of claim ~~94~~ wherein the first conductive layer comprises tungsten nitride.

Cont

99. (New) A method of treating a semiconductor device, comprising:

providing a first conductive layer and a dielectric formed on the first conductive layer; and

prior to forming the dielectric layer, exposing the first conductive layer to a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof to reduce the ability of the first conductive material to associate with oxygen.

100. (New) The method of claim 99 wherein the dielectric comprises tantalum pentoxide.

101. (New) The method of claim 99 wherein the first conductive layer comprises tungsten nitride.

Sub D4

102. (New) A method of treating a semiconductor device, comprising:

providing a first conductive plug, a first conductive layer on the plug, and a second conductive layer on the first conductive layer; and

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